

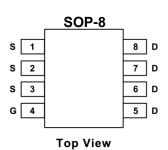
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NCE6005AS-HX

Dual N-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.040				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.055				
I _D (A) per leg	7				
Configuration	Dual				





- TrenchFET® Power MOSFET
- 100 % R_q and UIS tested

APPLICATIONS

- Load Switch
- **Battery Switch**

ABSOLUTE MAXIMUM RATINGS (Tc = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		VDS	60	V		
Gate-Source Voltage		Vgs	± 20			
Continuous Drain Current	T _C = 25 °C	ID	7			
	T _C = 125 °C		4			
Continuous Source Current (Diode Conduction) ^a		Is	3.6	Α		
Pulsed Drain Current ^b		IDМ	28			
Single Pulse Avalanche Current	L = 0.1 mH	IAS	18			
Single Pulse Avalanche Energy	L = 0.1 MH	Eas	16.2	mJ		
Maximum Power Dissipation b	T _C = 25 °C	PD	4	W		
Maximum Fower Dissipation =	T _C = 125 °C		1.3			
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to +175	°C		

Version 1.0 - 1 -Date: Jan. 2022



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Thermal	Characteristics								
Paramet	er			Symbol	Тур	M	ax Ur	nits	
Maximur	n Junction-to-Ambient ^A	t ≤ 10s		$R_{\Theta JA}$	50	62.	5 °C	°C/W	
Maximur	n Junction-to-Ambient ^A	Steady-Sta	ite		73	110) °C	°C/W	
Maximur	n Junction-to-Lead ^c	Steady-Sta	ıte	$R_{\Theta JL}$	31	40	°C	°C/W	
STATIC F	PARAMETERS								
Symbol	Parameter		Condition		Min	Тур	Max	Units	
BV _{DSS}	Drain-Source Breakdown V	oltage	I _D =250μ	A, V _{GS} =0V	60			V	
I _{DSS}	Zero Gate Voltage Drain Cu	urrent	V _{DS} =48\	/, V _{GS} =0V T _J =55°C			1 5	Α	
I_{GSS}	Gate-Body leakage current			V _{GS} = ±20V			100	nA	
$V_{GS(th)}$	Gate Threshold Voltage			I _D =250 A	1	2.1	3	V	
I _{D(ON)}	On state drain current			/, V _{DS} =5V	40			Α	
R _{DS(ON)}	Static Drain-Source On-Re	sistance	V _{GS} =10\	/, I _D =6.3A		20	25	mΩ	
D3(ON)	Ctatio Brain Course On Ite.	Sistanoc	\/ -4.5	T _J =125°C		34	42		
G	FITInd	<u> </u>	$V_{GS}=4.5$ $V_{DS}=5V$.	V, I _D =5.7A		22	30	mΩ	
V_{SD}	Forward Transconductance		50 - ,	2		27		S	
	Diode Forward Voltage			GS=UV		0.74	1	V	
l _S	Maximum Body-Diode Continuous Current					3	Α		
Pulsed Body Diode Current ^B							40	Α	
	C PARAMETERS							_	
C _{iss}	Input Capacitance		V _{GS} =0V,			1920	2300	pF	
C _{oss}	Output Capacitance V _{DS} =30			/, f=1MHz		155		pF	
C_{rss}	Reverse Transfer Capacita	nce				116		pF	
R_g	Gate resistance		V_{GS} =0 V , V_{DS} =0 V ,	f=1MHz		0.65	8.0	Ω	
	NG PARAMETERS								
Q _g (10V)	Total Gate Charge		•			47.6	58	nC	
• ,	Total Gate Charge		V _{GS} =10\	<i>I</i> ,		24.2	30	nC	
Q_{gs}	Gate Source Charge		\/ - 20	\/ I6 2A		6		nC	
Q_{gd}	Gate Drain Charge		v DS-30	V, I _D =6.3A		14.4		nC	
t _{D(on)}	Turn-On DelayTime	_	.,			7.6		ns	
t _r	Turn-On Rise Time		$V_{GS}=10\$ $V_{DS}=30\$			5		ns	
$t_{D(off)}$	Turn-Off DelayTime		$R_L=4.7\Omega,R_{GEN}=3\Omega$			28.9		ns	
t _f	Turn-Off Fall Time					5.5		ns	
t _{rr}	Body Diode Reverse Recov	ery Time	I _F =6.3A, dI/dt=10	0A/µs		33.2	40	ns	
Q_{rr}	Body Diode Reverse Recov	ery Charge	I _F =6.3A, dI/dt=10	0A/µs		43		nC	

Notes:

- A. The value of R $_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T $_A$ =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t \leq 10s thermal resistance rating.

- board design. The current rating is based on the LS 10s thermal resistance rating.

 B. Repetitive rating, pulse width limited by junction temperature.

 C. The R _{8JA} is the sum of the thermal impedence from junction to lead R _{JL} and lead to ambient.

 D. The static characteristics in Figures 1 to 6 are obtained using <300 s pulses, duty cycle 0.5% max.

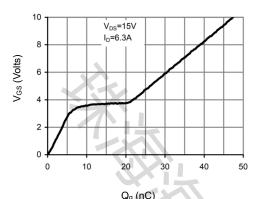
 E. These tests are performed with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with T _A=25°C.

Version 1.0 - 2 -Date: Jan. 2022

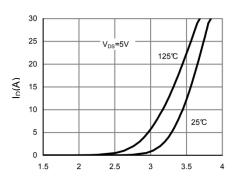


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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



Q_g (nC)
Gate-Charge Characteristics Fig 1.



V_{GS}(Volts)
Fig 2. Transfer Characteristics

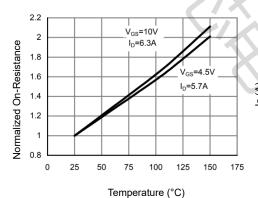


Fig 3. On-Resistance vs. Junction Temperature

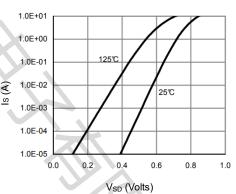


Fig 4. Body-Diode Characteristics

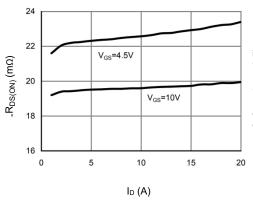


Fig 5. On-Resistance vs. Drain Current and **Gate Voltage**

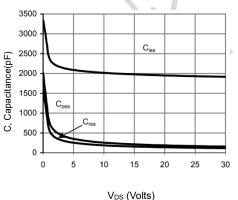
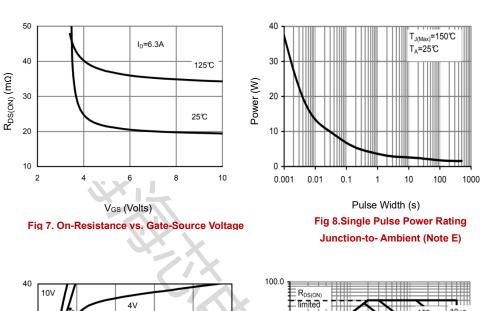


Fig 6. Capacitance Characteristics

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



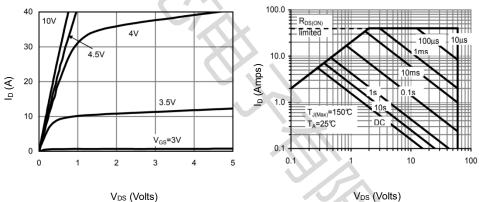


Fig 9. On-Region Characteristics



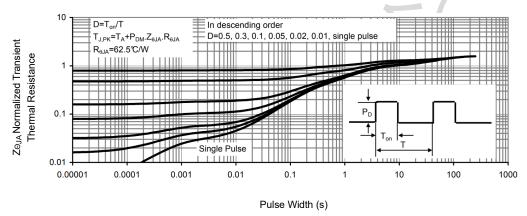


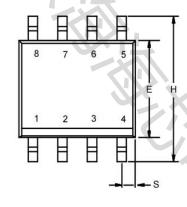
Fig 11. Normalized Maximum Transient Thermal Impedance

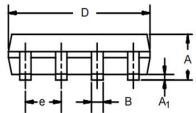
Version 1.0 - 4 -Date: Jan. 2022

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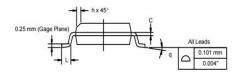
SOP-8 Package Outline

Dimensions are shown in millimeters (inches)





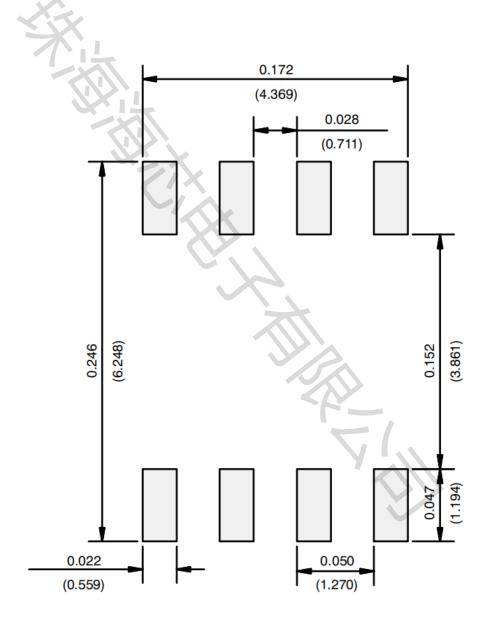
DIM	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.2	27 BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	



- 5 -Date: Jan. 2022 Version 1.0

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RECOMMENDED MINIMUM PADS FOR SOP-8

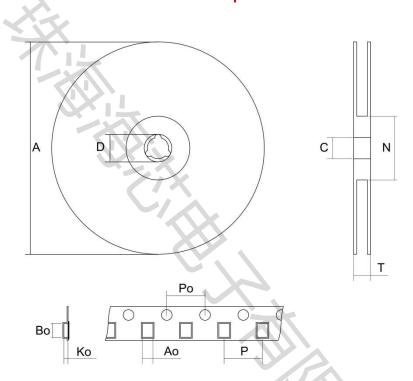


Version 1.0 - 6 -Date: Jan. 2022

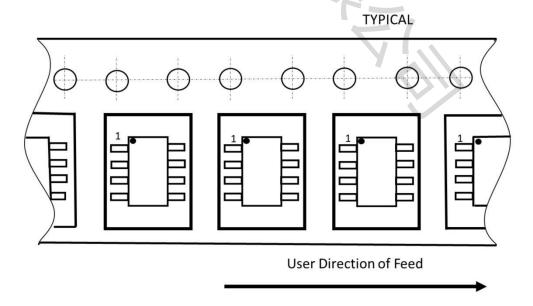
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SOP-8 packing information

SOP-8 tape and reel



Tape orientation



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Version 1.0 - 8 - Date: Jan. 2022